



On the constitution and thermodynamic modelling of the system Zr-Ni-Sn



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ABSTRACT

In continuation of our optimization of {Ti,Zr}NiSn-based thermoelectrics, we herein determined the constitution of the system Zr-Ni-Sn (liquidus surface and isothermal section at 950 °C) employing X-ray powder diffraction (XPD) and electron probe micro analysis (EPMA) of about 80 ternary alloys in as cast and annealed state. The system is characterized by the existence of four ternary compounds labelled τ_1 to τ_4 . At 950 °C no significant homogeneity regions are found for the compounds τ_1 -ZrNiSn (Half-Heusler phase, MgAgAs-type), τ_2 -ZrNi₂Sn (Heusler phase, MnCu₂Al-type) and τ_4 -Zr₆NiSn₂ (K₂UF₆-type, ordered Fe₂P-type), but τ_3 -Zr_{2+x}Ni_{2+y}Sn_{1-x-y} exhibits a significant solution range for 0.0 ≤ x ≤ 0.25 and 0.0 ≤ y ≤ 0.06. Extended solid solutions starting from binary phases at 950 °C have been evaluated for Zr₅(Ni_x□_ySn_{1-x-y})₄ (filled Mn₅Si₃ - Ti₅Ga₄-type; 0 ≤ x ≤ 0.216, 0.002 ≤ y ≤ 1) and Zr_{1-x}(Ni_{1-y}Sn_y)_{5+x} (AuBe₅-type) reaching a maximum solubility at x = 0.022, y = 0.146 (the symbol □ denotes a vacancy). From differential thermal analysis (DTA) measurements a complete liquidus surface has been elucidated revealing congruent melting for τ_1 -ZrNiSn (at 1465 ± 10 °C) and τ_2 -ZrNi₂Sn at 1469 ± 10 °C, but incongruent melting for τ_3 -Zr₂Ni₂Sn (pseudobinary peritectic formation: $\ell + \text{Zr}_5(\text{Ni}_x\text{□}_y\text{Sn}_{1-x-y})_4 \leftrightarrow \tau_3$ at 1406 ± 10 °C), and for τ_4 -Zr₆NiSn₂ (ternary P-type reaction: $\text{L} + \text{Zr}_5(\text{Ni}_x\text{□}_y\text{Sn}_{1-x-y})_4 + (\text{Zr}) \leftrightarrow \tau_4$ -Zr₆NiSn₂ at 1124 ± 8 °C). A Schultze-Scheil diagram for the solidification behavior was constructed for the entire diagram. X-ray single crystal data have defined precise atom site occupancies in τ_4 -Zr₆NiSn₂ ($R_{p2} = 0.0113$) as well as close to the end point of the solid solution Zr₅Ni_{1-x}Sn₃ (stuffed Mn₅Si₃-type; x = 0.21, $R_{p2} = 0.0238$) and isostructural Hf₅Ni_{1-x}Sn₃ (x = 0.26, $R_{p2} = 0.0242$). As thermodynamic data in the ternary system were only available in the literature for ZrNiSn, heat of formation data were supplied by our DFT calculations for ZrNi₂Sn, Zr₂Ni₂Sn and Zr₆NiSn₂ as well as for the solid solutions Zr₅(Ni_x□_ySn_{1-x-y})₄ and Zr_{1-x}(Ni_{1-y}Sn_y)_{5+x} for y = 0 and x = 0.25 or y = 0.20. For these cases DFT calculations also provide details on electronic properties and bonding. Thermodynamic CALPHAD calculation was performed with the Pandat software and resulted in reasonably good agreement for all the 29 invariant reaction isotherms involving the liquid.

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1. Introduction

Quinary (i.e. quasi-ternary) solid solutions of the so-called “Half-

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Heusler” (HH) compounds TiNiSn, ZrNiSn and HfNiSn, known as n-type semiconductors since 1986 [1,2], have proven a remarkably high efficiency in thermoelectric conversion of (waste) heat into electricity: a dimensionless thermoelectric figure of merit $ZT = 1.5$ was reached at 700 K for the alloy $\text{Ti}_{0.5}\text{Zr}_{0.25}\text{Hf}_{0.25}\text{NiSn}_{0.998}\text{Sb}_{0.002}$ slightly doped with Sb [3]. In order to avoid the high-price element hafnium, recent thermoelectric research focused mainly on the optimization